

GigaMOS™ Power MOSFET

IXFK230N20T IXFX230N20T

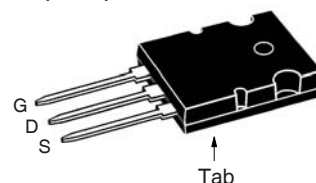
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



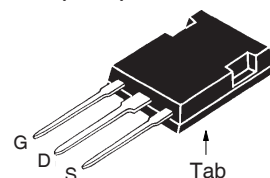
$$\begin{aligned} V_{DSS} &= 200V \\ I_{D25} &= 230A \\ R_{DS(on)} &\leq 7.5m\Omega \\ t_{rr} &\leq 200ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	200	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	200	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$ (Chip Capability)	230	A
$I_{L(RMS)}$	External Lead Current Limit	160	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	630	A
I_A	$T_C = 25^\circ C$	100	A
E_{AS}	$T_C = 25^\circ C$	5	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 175^\circ C$	20	V/ns
P_D	$T_C = 25^\circ C$	1670	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in
F_C	Mounting Force (PLUS247)	20..120 / 4.5..27	N/lb
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Synchronous Rectification
- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3mA$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8mA$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ C$			50 μA 3 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 60A$, Note 1			7.5 m Ω

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10V, I_D = 60A$, Note 1	90	150	S
C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		24	nF
C_{oss}			2440	pF
C_{rss}			60	pF
R_{Gi}	Gate Input Resistance		1.15	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		58	ns
t_r			38	ns
$t_{d(off)}$			62	ns
t_f			17	ns
$Q_{g(on)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		358	nC
Q_{gs}			138	nC
Q_{gd}			60	nC
R_{thJC}			0.09	$^{\circ}C/W$
R_{thCS}			0.15	$^{\circ}C/W$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0V$			230 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			920 A
V_{SD}	$I_F = 60A, V_{GS} = 0V$, Note 1			1.3 V
t_{rr}	$I_F = 115A, -di/dt = 100A/\mu s$ $V_R = 75V, V_{GS} = 0V$		0.74	ns
Q_{RM}				μC
I_{RM}			10.6	A

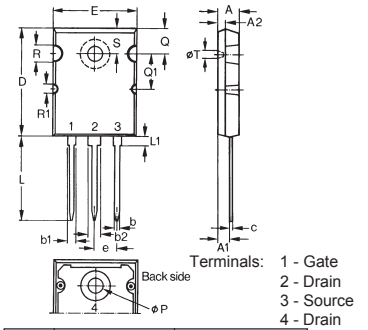
Note 1: Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

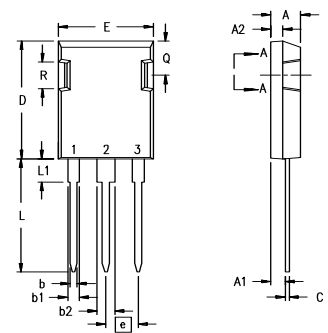
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS 247™ Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

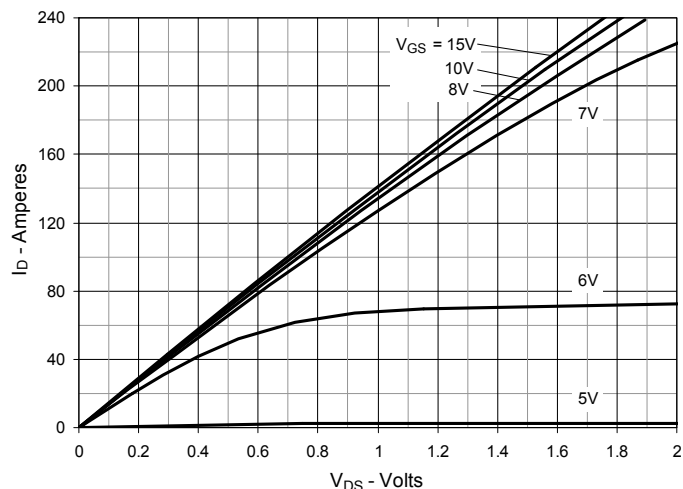


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

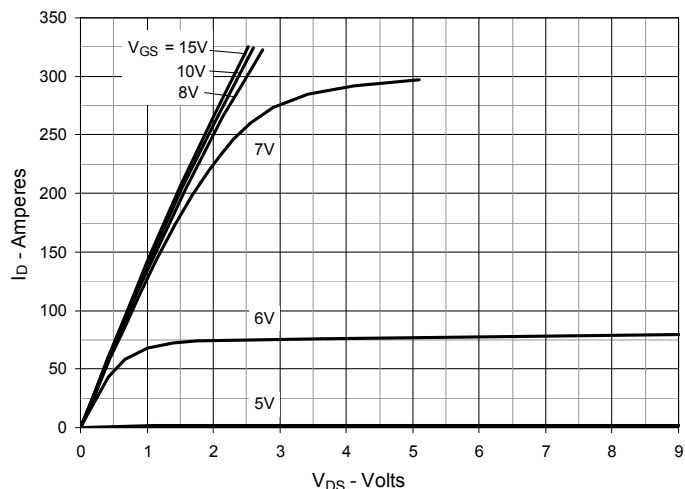


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

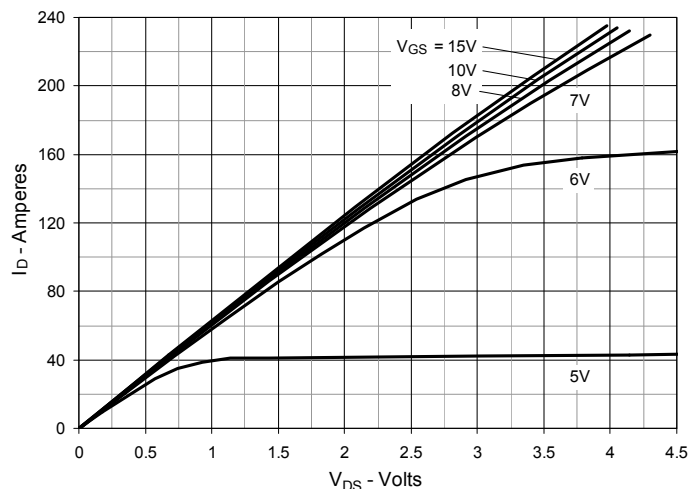


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 115\text{A}$ Value vs. Junction Temperature

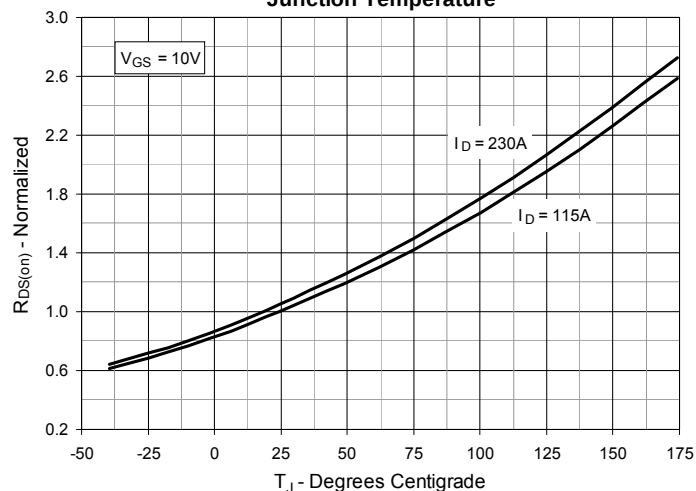


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 115\text{A}$ Value vs. Drain Current

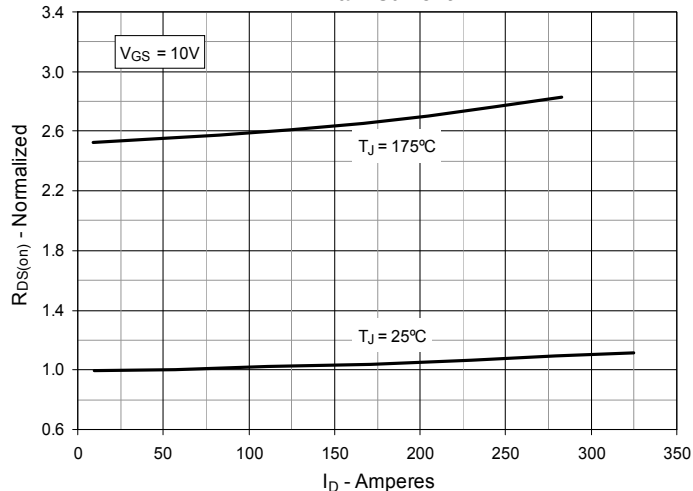


Fig. 6. Drain Current vs. Case Temperature

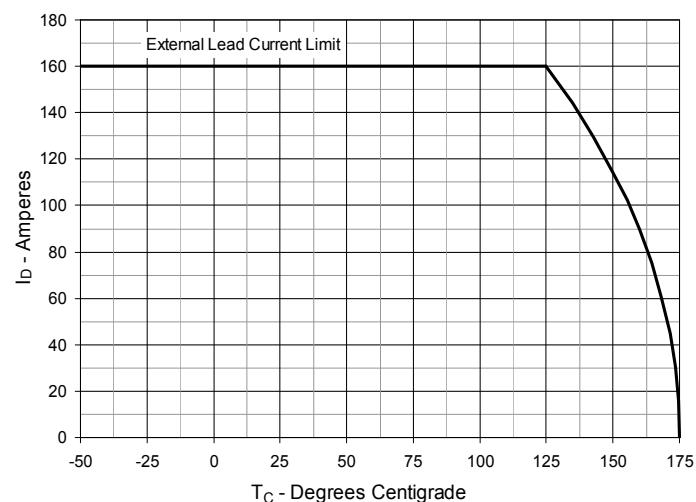


Fig. 7. Input Admittance

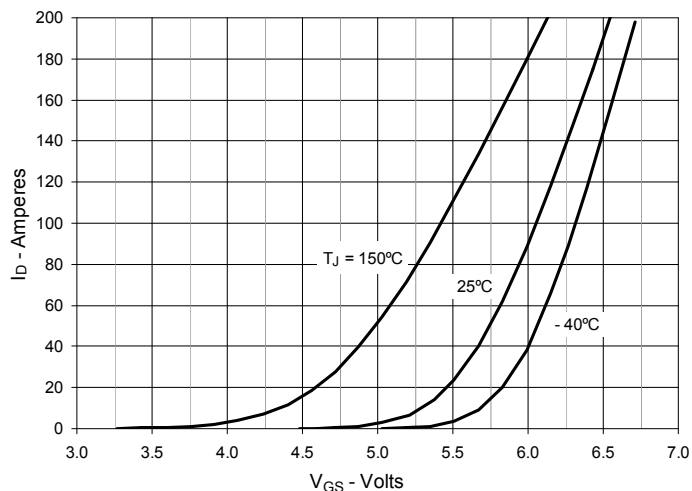


Fig. 8. Transconductance

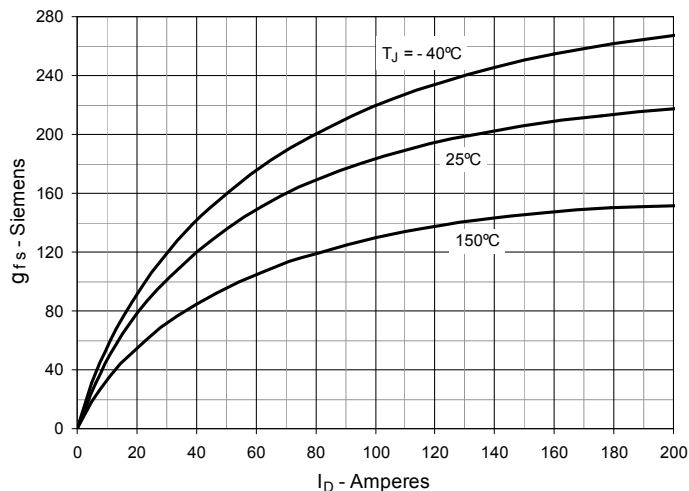


Fig. 9. Forward Voltage Drop of Intrinsic Diode

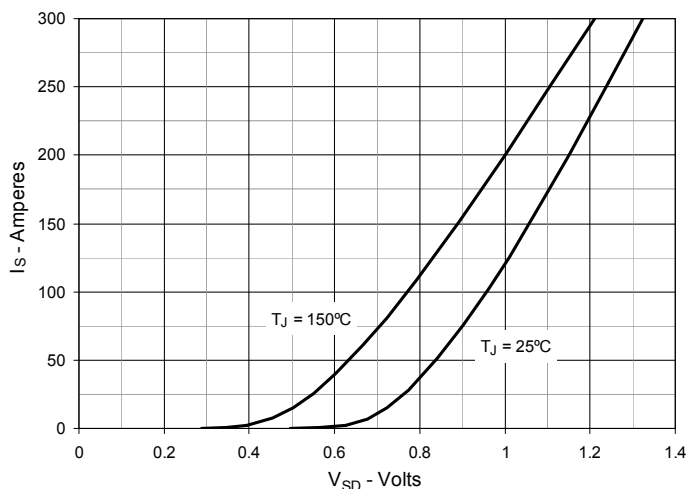


Fig. 10. Gate Charge

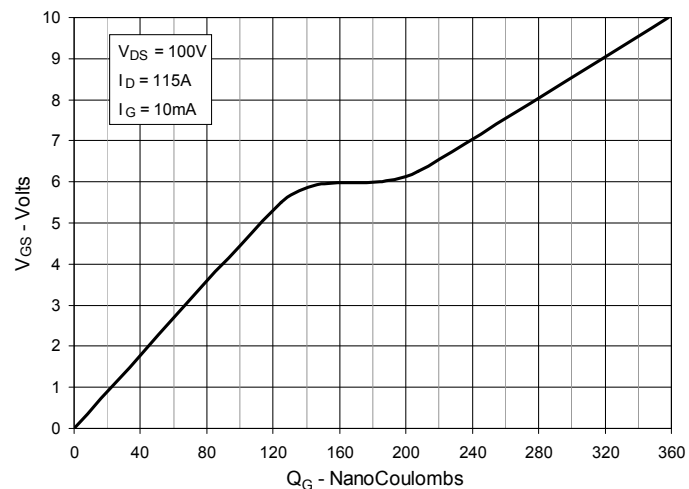


Fig. 11. Capacitance

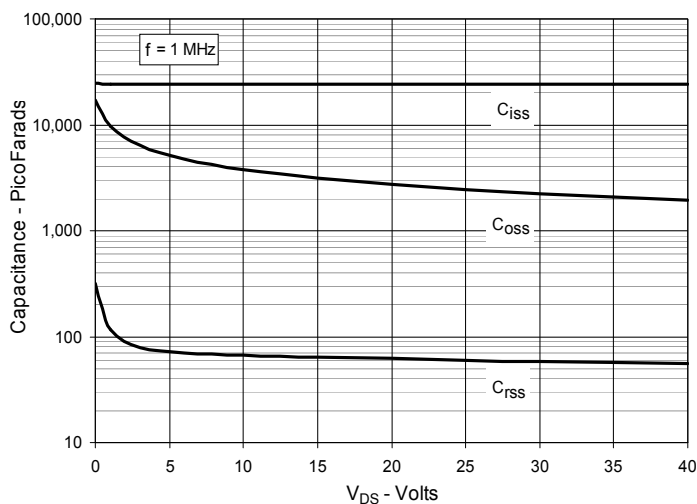


Fig. 12. Forward-Bias Safe Operating Area

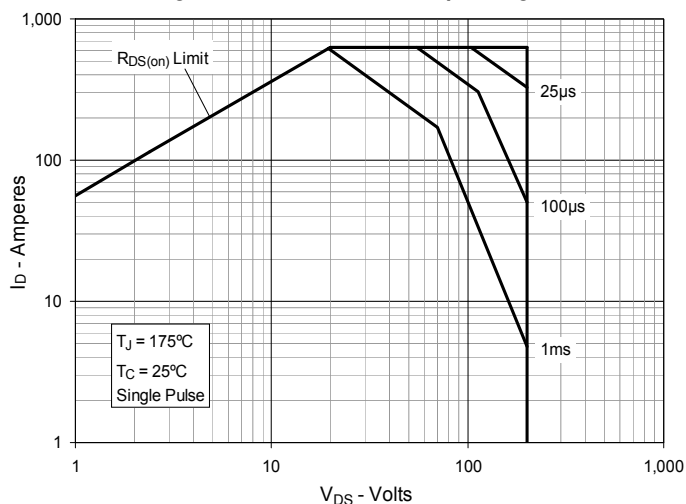


Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature

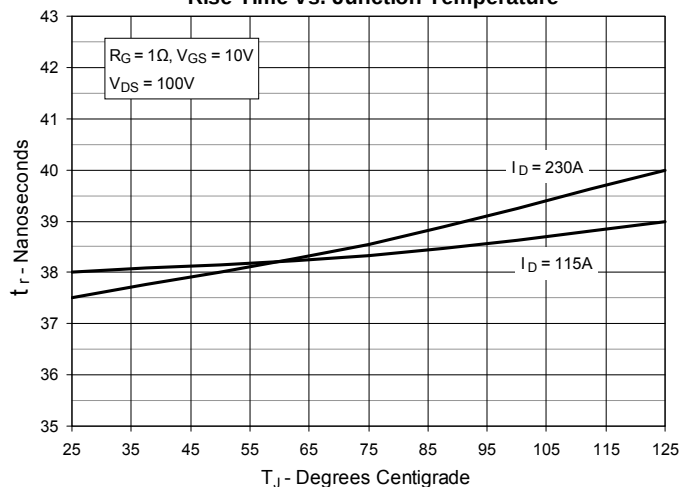


Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current

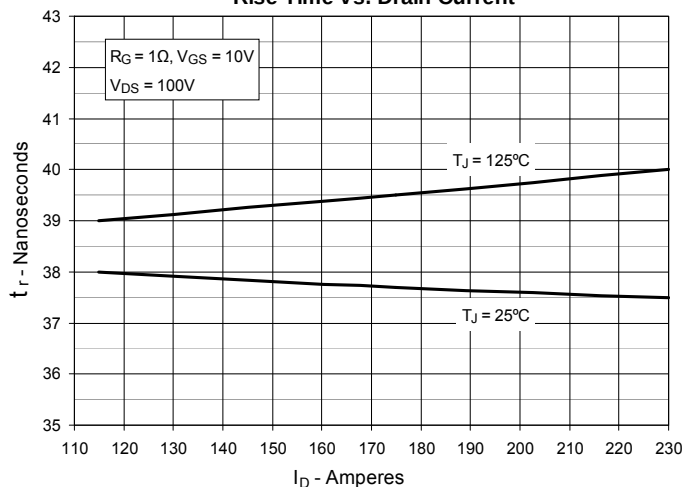


Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance

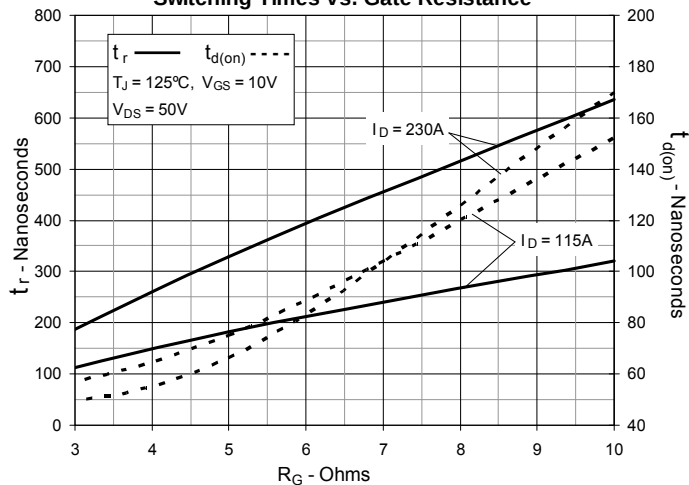


Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature

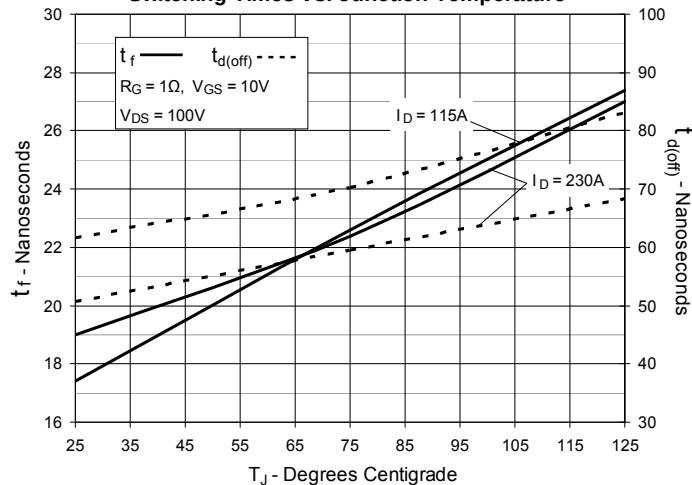


Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current

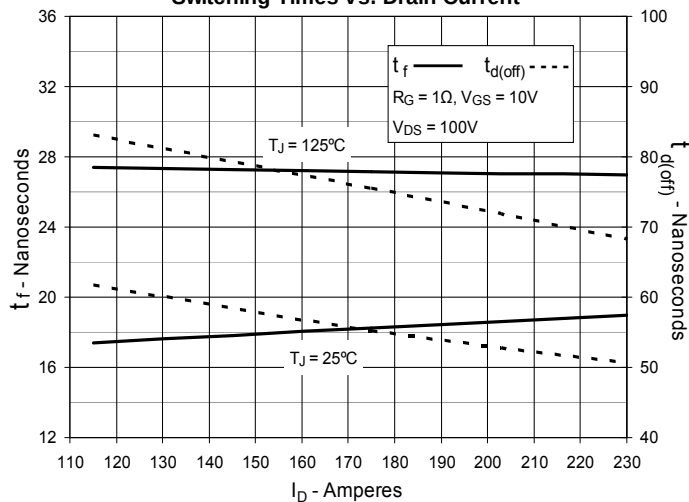


Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance

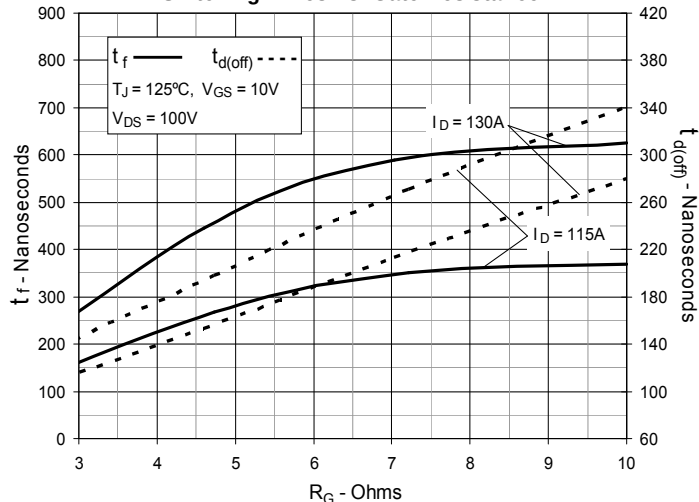


Fig. 19. Maximum Transient Thermal Impedance

